

In the Claims

Claims 39-42 and 46-50 are pending in the application with claims 43-45 canceled herein.

Claims 1-35 (cancelled).

39. (previously presented) A semiconductor processing method of electrochemical-mechanical removing at least some of a conductive material from over an upper surface of a semiconductor substrate comprising:

displacing a polishing operation location across the upper surface of the substrate from a central region of the substrate toward a periphery of the substrate and not displacing the polishing operation location from the periphery to the central region, the polishing operation location being defined by a location of a polishing pad relative to a surface of the substrate; and

rotating both the polishing pad and the substrate separately from the displacement.

40. (previously presented) The method of claim 39 wherein the polishing pad is rotated in counter-rotary manner relative to the rotation of the substrate.

41. (previously presented) The method of claim 39 wherein the polishing pad comprises a flexible material and has peripheral edges that are raised relative to a center of the polishing pad.

42. (previously presented) The method of claim 39 wherein a polishing surface of the polishing pad extends over only a portion of the surface of the substrate.

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Claims 43-45 (cancelled).

46. (previously presented) A semiconductor processing method of removing conductive material, comprising:

providing a semiconductor wafer having a conductive material thereover, the wafer comprising an upper surface and an outer periphery around the upper surface, the conductive material extending across the upper surface of the wafer and to about the periphery;

electrochemically removing at least some of the conductive material with a polishing pad having a surface in abrasive contact with only a portion of the conductive material;

displacing the polishing pad across the upper surface of the wafer during the removing, the displacing being only from a central region of the wafer surface toward the periphery of the wafer;

rotating at least one of the polishing pad and the wafer separately from the displacement; and

providing an electrical circuit through at least a portion of the conductive material during the removing, the circuit extending between at least one second electrical connection in electrical contact with a polishing surface of the polishing pad and at least one first electrical connection in direct electrical contact with conductive material only at the periphery.

47. (previously presented) The method of claim 46 wherein the polishing pad is displaced circularly around the central region to define rings which progress increasingly outward toward the periphery of the wafer.

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48. (previously presented) The method of claim 46 comprising rotating both the polishing pad and the wafer where the polishing pad is rotated in counter-rotary manner relative to the rotation of the wafer.

49. (previously presented) The method of claim 46 wherein the polishing pad comprises a flexible material and has peripheral edges that are raised relative to a center of the polishing pad.

50. (previously presented) The method of claim 46 wherein a polishing surface of the polishing pad extends over only a portion of the surface of the substrate.